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63/019,563 04 May 2020 (04.05.2020) US</p> <p>(71) Applicant: LAM RESEARCH CORPORATION [US/US]; 4650 Cushing Parkway, Fremont, California 94538 (US).</p> <p>(72) Inventors: GUO, Tongtong; 4650 Cushing Parkway, Fremont, California 94538 (US). BATZER, Rachel E.; 4650 Cushing Parkway, Fremont, California 94538 (US). QIU, Huatan; 4650 Cushing Parkway, Fremont, California 94538 (US). CHEN, Lee; 4650 Cushing Parkway, Fremont, California 94538 (US). GONG, Bo; 4650 Cushing</p> | <p>Parkway, Fremont, California 94538 (US). GUI, Zhe; 4650 Cushing Parkway, Fremont, California 94538 (US).</p> <p>(74) Agent: SRINIVASAN, Arthi G. et al.; Weaver Austin Villeneuve & Sampson LLP, P. O. Box 70250, Oakland, California 94612-0250 (US).</p> <p>(81) Designated States (<i>unless otherwise indicated, for every kind of national protection available</i>): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.</p> <p>(84) Designated States (<i>unless otherwise indicated, for every kind of regional protection available</i>): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,</p> |
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(54) Title: INCREASING PLASMA UNIFORMITY IN A RECEPTACLE

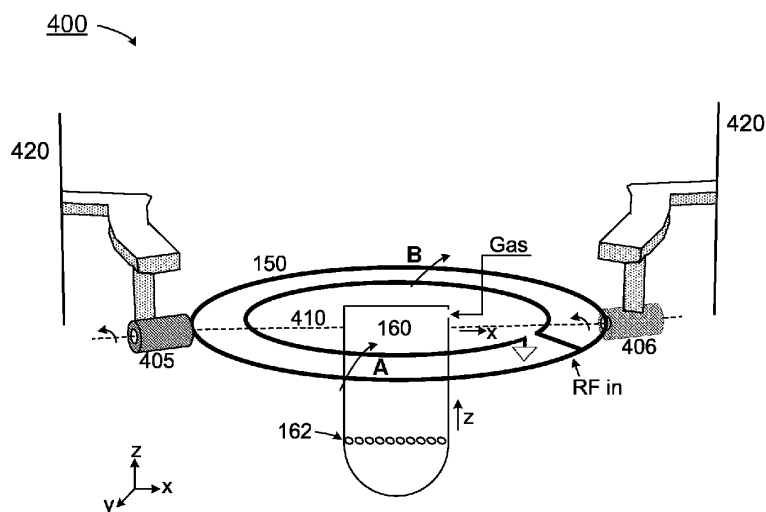


FIG. 4A

(57) **Abstract:** An apparatus for forming a plasma may include one or more coupling ports to accept and RF current. The apparatus may additionally include a receptacle to accommodate one or more gases, in which the receptacle is oriented along a first axis. The apparatus may additionally include an RF coupling structure, oriented in a plane and substantially surrounding the receptacle, the RF coupling structure can be configured to conduct an RF current to bring about formation of the plasma within the receptacle. The apparatus may further include one or more linkages, coupled to the RF coupling structure, which may permit the plane of the RF coupling structure to pivot about a second axis so as to tilt the plane of the RF coupling structure toward the first axis.

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